



HM40N25 / HM40N25F

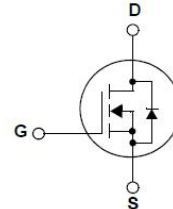
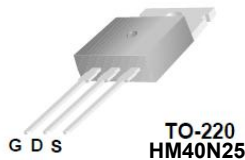
250V N-Channel MOSFET

General Description

This Power MOSFET is produced using H&M semi's advanced planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

Features

- 40A, 250V, $R_{DS(on) typ.} = 0.079\Omega @ V_{GS} = 10V$
- Low gate charge (typical 55 nC)
- High ruggedness
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	HM40N25	HM40N25F	Units
V_{DSS}	Drain-Source Voltage	250		V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	40	40 *	A
		28	28 *	A
I_{DM}	Drain Current - Pulsed (Note 1)	120	120 *	A
V_{GSS}	Gate-Source Voltage	± 30		V
EAS	Single Pulsed Avalanche Energy (Note 2)	1120		mJ
I_{AR}	Avalanche Current (Note 1)	40		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	25.6		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	256	41.8	W
		2.05	0.34	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to $+150$		$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		$^\circ\text{C}$

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	HM40N25	HM40N25F	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.49	3.0	$^\circ\text{C/W}$
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ\text{C/W}$

Package Marking

Part Number	Top Marking	Package	Packing Method	MOQ	QTY
HM38N25	HM38N25	T0-220C	Tube	1000	5000
HM38N25F	HM38N25F	T0-220F	Tube	1000	5000

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	250	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.26	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 200\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 19\text{ A}$	--	0.079	0.01	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 19\text{ A}$ (Note 4)	--	22	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1560	--	pF
C_{oss}	Output Capacitance		--	370	--	pF
C_{rss}	Reverse Transfer Capacitance		--	150	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 125\text{ V}, I_D = 40\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4, 5)	--	30	--	ns
t_r	Turn-On Rise Time		--	35	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	150	--	ns
t_f	Turn-Off Fall Time		--	85	--	ns
Q_g	Total Gate Charge	$V_{DS} = 200\text{ V}, I_D = 40\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	55	--	nC
Q_{gs}	Gate-Source Charge		--	12	--	nC
Q_{gd}	Gate-Drain Charge		--	23	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	40	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	120	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 40 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 40 A,	--	220	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/us (Note 4)	--	2.0	--	uC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $I_{AS} = 40\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 40\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

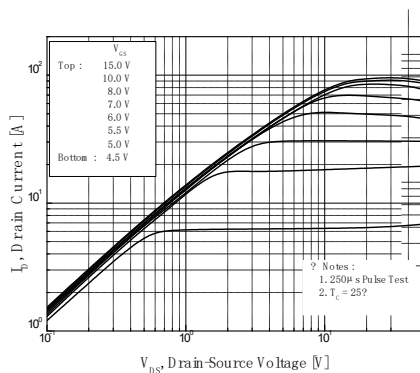


Figure 1. On-Region Characteristics

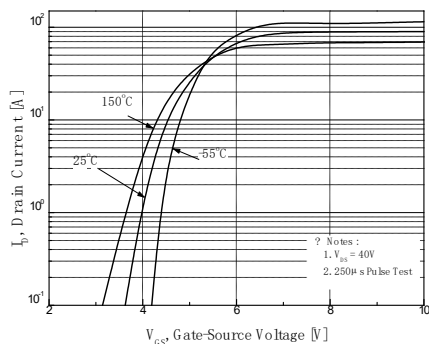


Figure 2. Transfer Characteristics

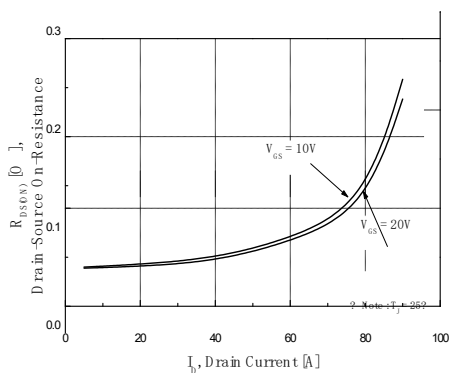


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

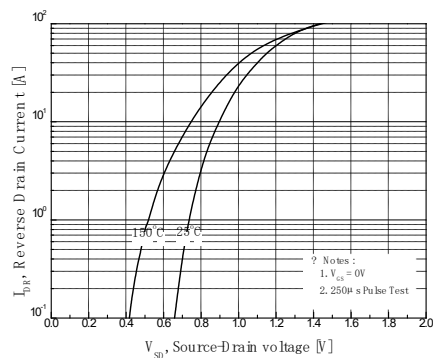


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

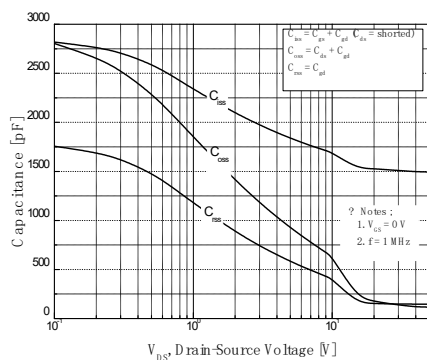


Figure 5. Capacitance Characteristics

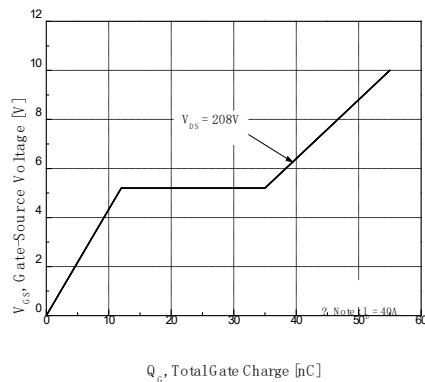


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

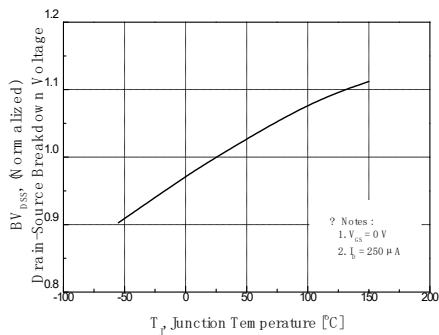


Figure 7. Breakdown Voltage Variation vs Temperature

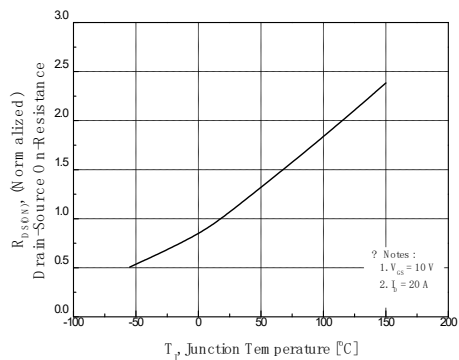


Figure 8. On-Resistance Variation vs Temperature

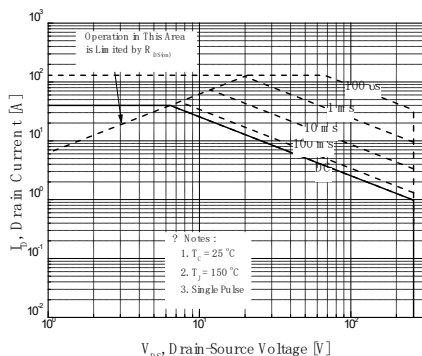


Figure 9-1. Maximum Safe Operating Area for HM40N25

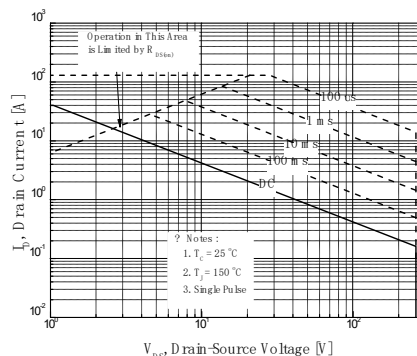


Figure 9-2. Maximum Safe Operating Area for HM40N25

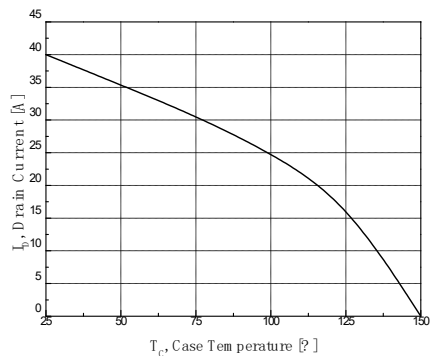


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

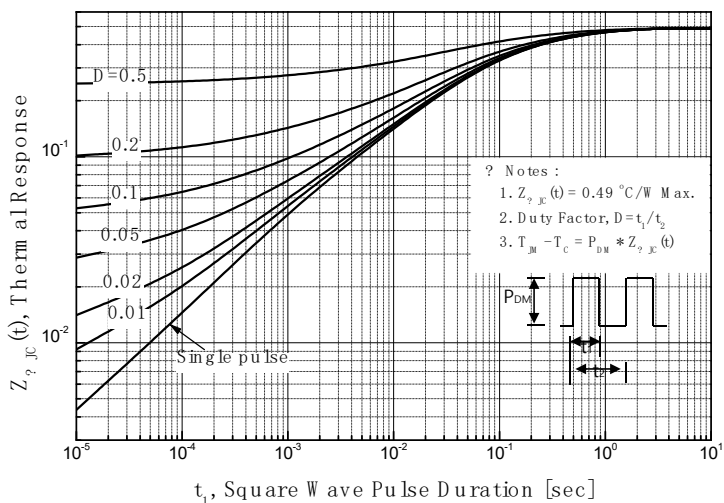


Figure 11-1. Transient Thermal Response Curve for HM40N25

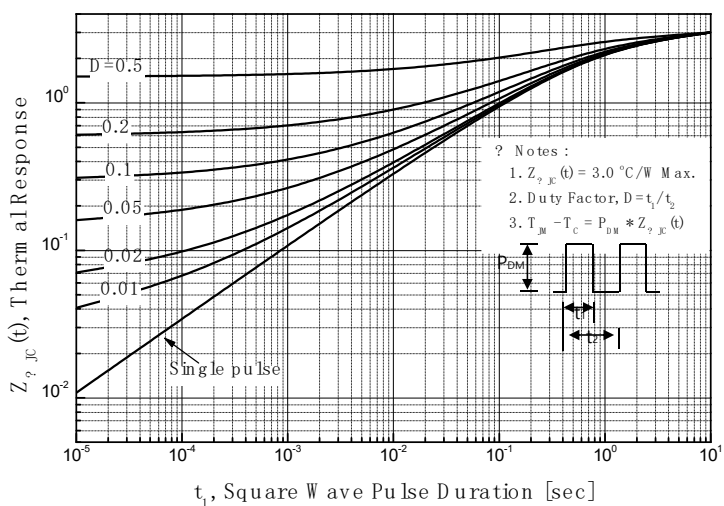
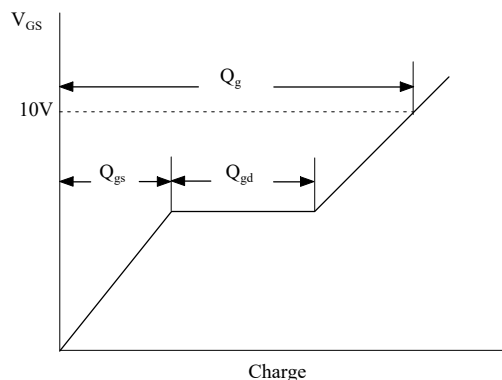
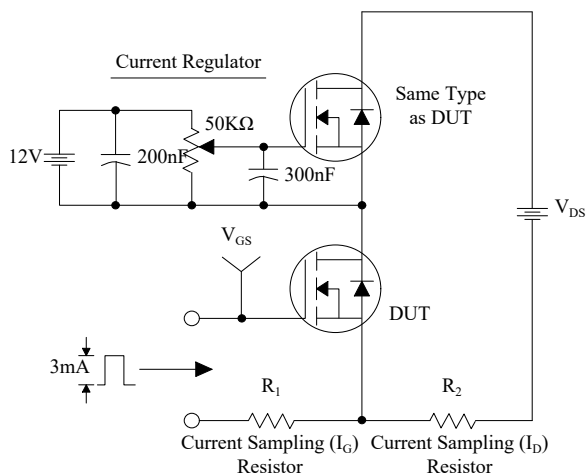
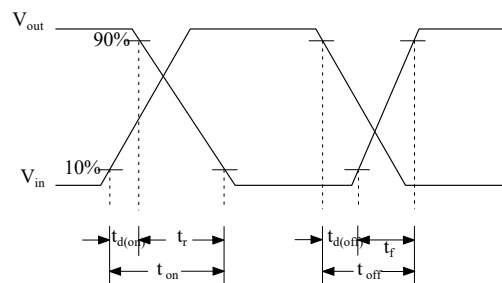
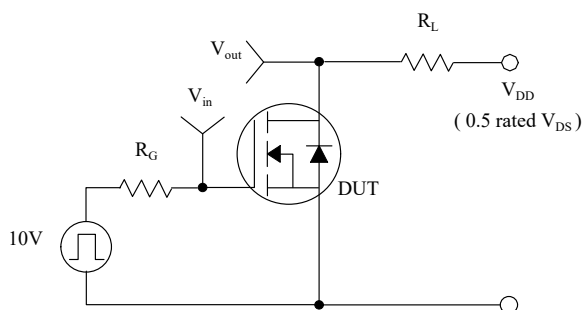


Figure 11-2. Transient Thermal Response Curve for HM40N25

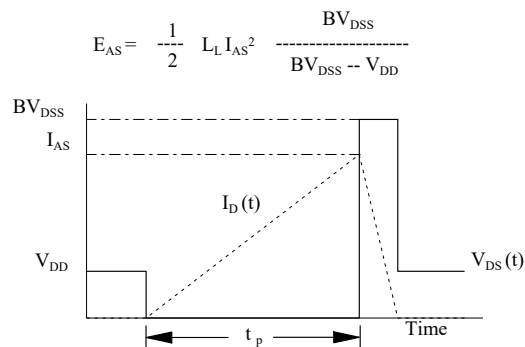
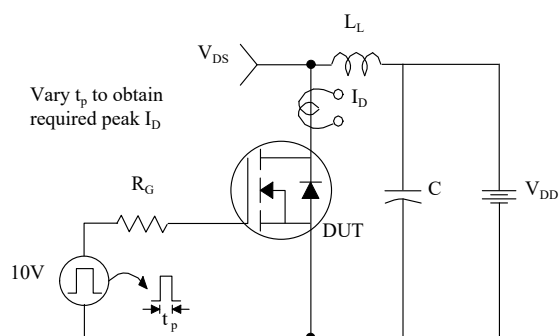
Gate Charge Test Circuit & Waveform



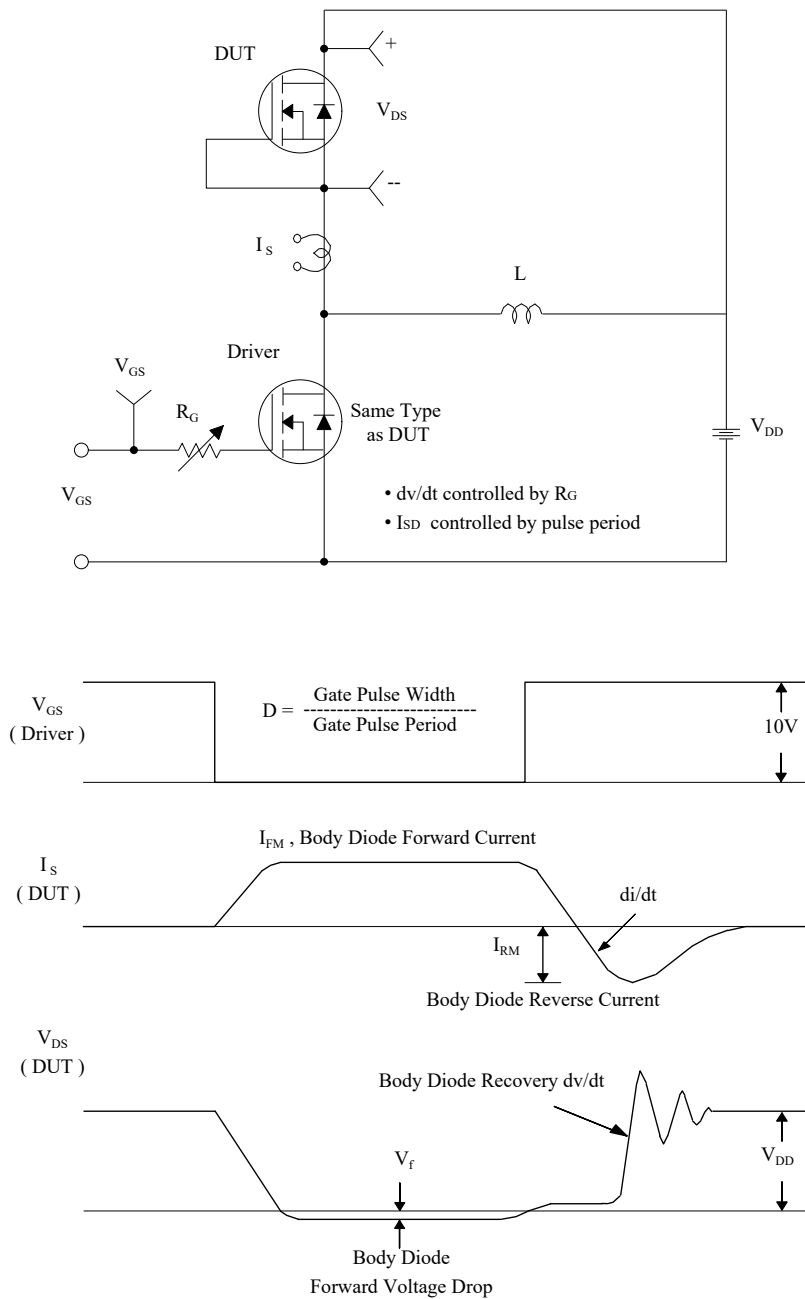
Resistive Switching Test Circuit & Waveforms



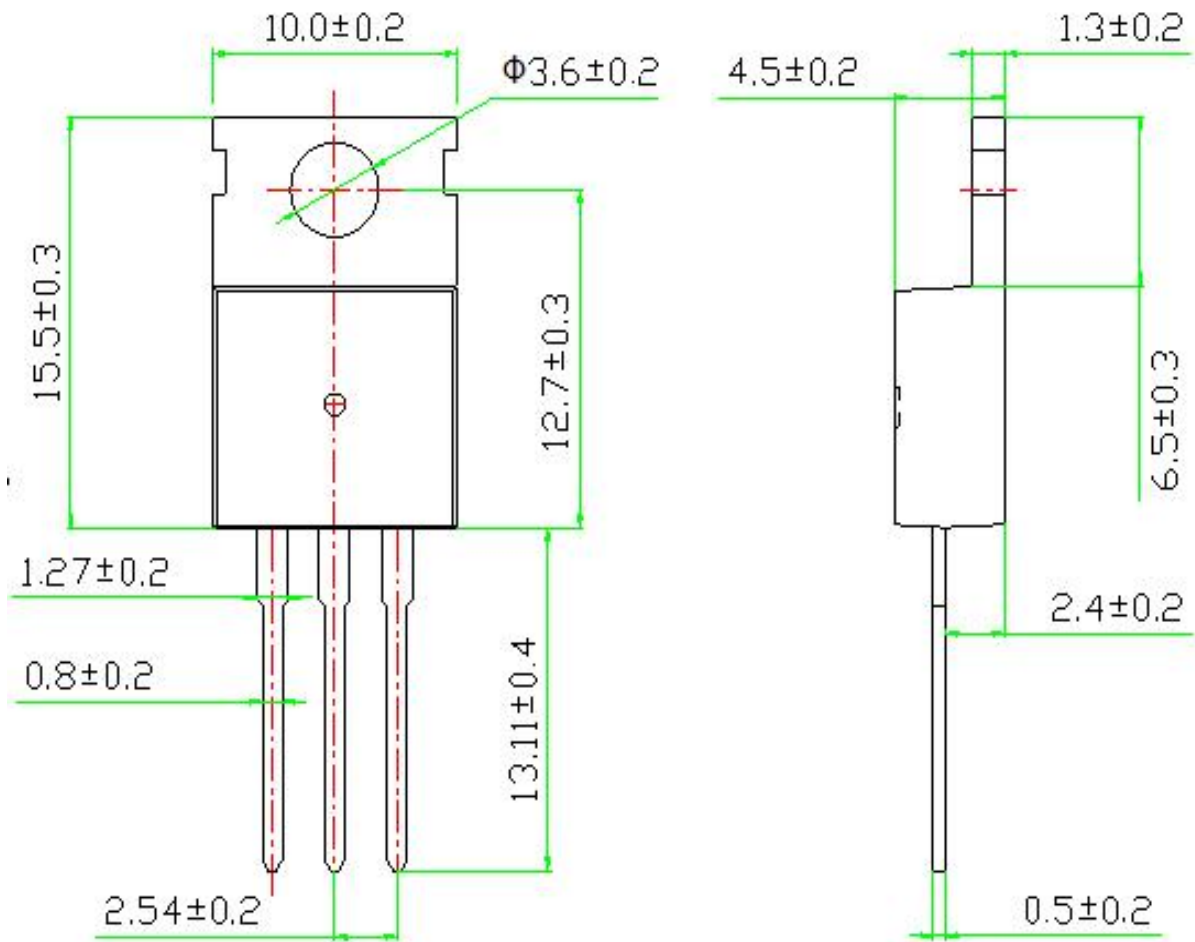
Unclamped Inductive Switching Test Circuit & Waveforms

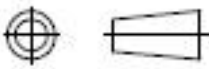


Peak Diode Recovery dv/dt Test Circuit & Waveforms

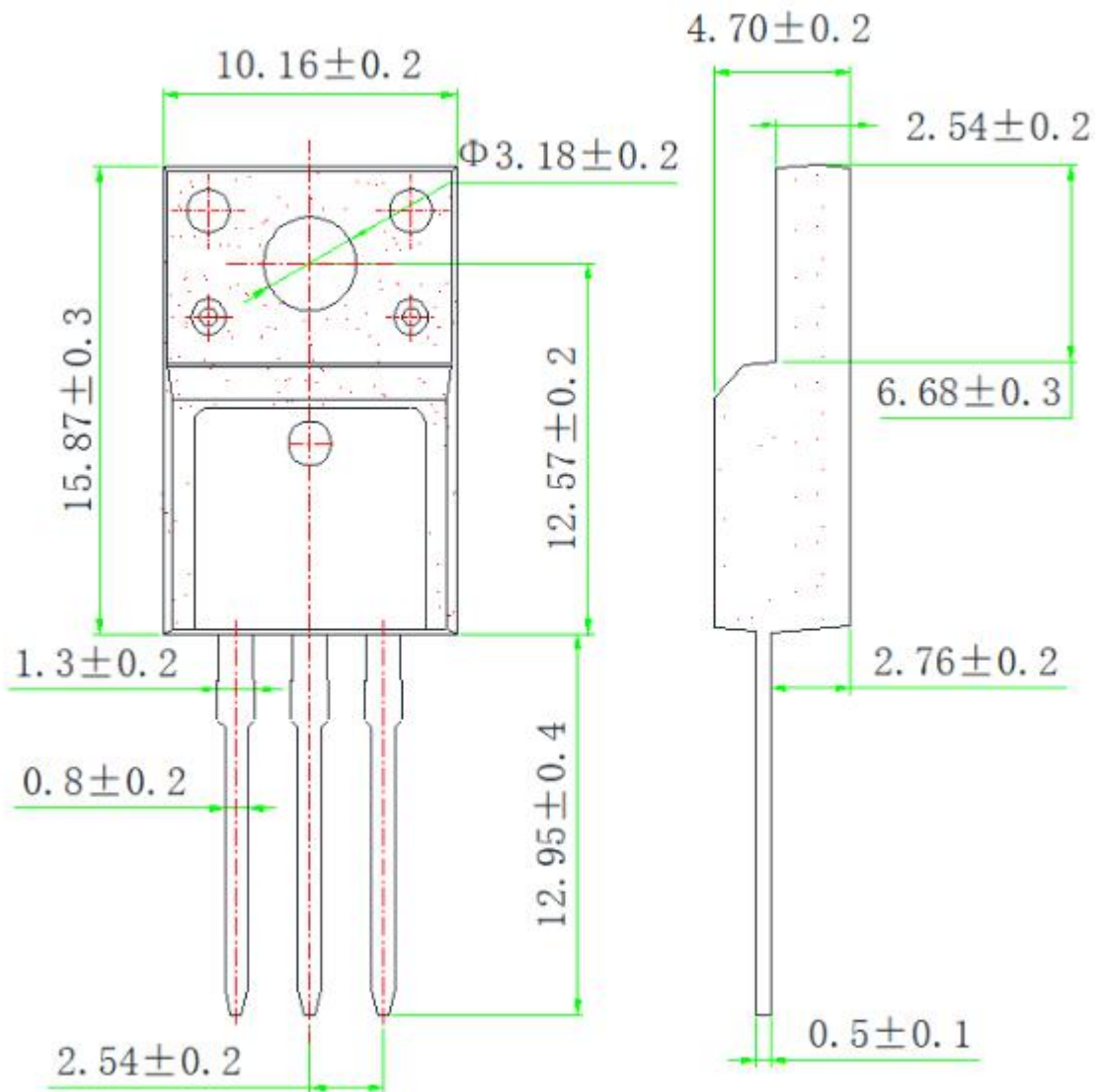


TO-220C OUTLINE



NAME	TO-220C OUTLINE	UNIT	mm	DESIGNED	Shawn Chen	THIRD ANGLE SYSTEM
DWGNO		PAGE	1 OF 1	CHECKED		
VERSION	Ver1.0	ISSUE DATE		APPROVED		

TO-220F OUTLINE



NOTE:

1The plastic package is not marked as smooth surface $R_a = 0.1$; Subglossy surface $R_a = 0.8$

2.Undeclared tolerance ± 0.25 , Unmarked fillet $R_{max} = 0.25$